(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
15 October 2009 (15.10.2009)

PCT

(10) International Publication Number
WO 2009/126412 A1

(51) International Patent Classification:
H01L 23/544 (2006.01) *H01L 21/60* (2006.01)
H01L 25/065 (2006.01) *H01L 29/06* (2006.01)
H01L 21/98 (2006.01) *H01L 23/48* (2006.01)

(21) International Application Number:
PCT/US2009/037418

(22) International Filing Date:
17 March 2009 (17.03.2009)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
12/101,776 11 April 2008 (11.04.2008) US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Declarations under Rule 4.17:

— *as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii))*

— *as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))*

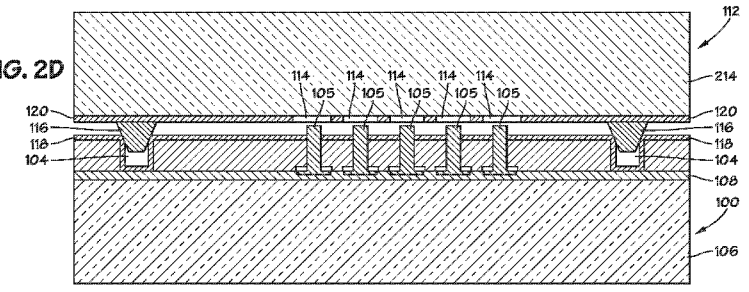
Published:

— *with international search report (Art. 21(3))*

— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments (Rule 48.2(h))*

(54) Title: METHOD OF CREATING ALIGNMENT/CENTERING GUIDES FOR SMALL DIAMETER, HIGH DENSITY THROUGH-WAFER VIA DIE STACKING

FIG. 2D



(57) Abstract: A method is provided for forming a die stack. The method includes forming a plurality of through-wafer vias (105) and a first plurality of alignment features (104) in a first die. A second plurality of alignment features (116) is formed in a second die, and the first die is stacked on the second die such that the first plurality of alignment features engage the second plurality of alignment features. A method of manufacturing a die stack is also provided that includes forming a plurality of through- wafer vias on a first die, forming a plurality of recesses (104) on a first die, and forming a plurality of protrusions (116) on a second die. A die stack and a system are also provided.

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